

grinding the back of the semiconductor wafer while protecting the semiconductor wafer surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate having a thickness and Young's modulus whose product is in the range of 0.5 to 100 kg/cm and said substrate exhibiting a maximum value of dynamic viscoelasticity  $\tan \delta$  of 0.78 to 1.61 at a temperature ranging from  $-5$  to  $80^{\circ}\text{C}$ .

#### **REMARKS**

Claims 1-8 are pending in the present application. Claims 1-4 have been cancelled. Claims 5-8 have been amended to read in independent form. Claims 5 and 7 include the limitations of cancelled claims 1 and 3. Claims 6 and 8 include the limitations of cancelled claims 1, 2, and 4. The amendments place the claims in better form for appeal. The amendments are supported in the original claims and at page 2, lines 3-18, of the specification. Applicants appreciate the Examiner's indication of allowable subject matter in claims 5-8.

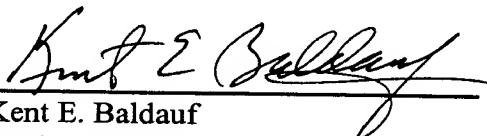
The cancellation of claims 1-4 renders the rejected under 35 U.S.C. § 102(b) moot, and as such, it should be withdrawn.

The Examiner has objected to claims 5-8 as being dependant upon a rejected base claim. Claims 5-8 have been amended to read in independent form. Claims 5 and 7 include the limitations of cancelled claims 1 and 3. Claims 6 and 8 include the limitations of cancelled claims 1, 2, and 4. Thus, the Examiner's objection has been fully satisfied and should be withdrawn.

Accordingly, in view of the foregoing remarks, it is believed that the present application is in condition for allowance. Reconsideration of the objection and allowance of claims 5-8 are respectfully requested.

Respectfully submitted,

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**Marked-Up Versions of Claims 5, 6, 7, and 8**

5. [The] A method [as claimed in claim 3, wherein the] of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of an adherend that has a surface having a height difference of at least 30  $\mu\text{m}$  and working the adherend at its back while protecting the adherend surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate exhibiting a maximum value of dynamic viscoelasticity  $\tan \delta$  of 0.78 to 1.61 at a temperature ranging from  $-5$  to  $80^{\circ}\text{C}$ .

6. [The] A method [as claimed in claim 4, wherein the] of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of an adherend that has a surface having a height difference of at least 30  $\mu\text{m}$  and working the adherend at its back while protecting the adherend surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate having a thickness and Young's modulus whose product is in the range of 0.5 to 100 kg/cm and said substrate exhibiting a maximum value of dynamic viscoelasticity  $\tan \delta$  of 0.78 to 1.61 at a temperature ranging from  $-5$  to  $80^{\circ}\text{C}$ .

7. [The] A method [as claimed in claim 3, wherein the adherend is a] of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of a semiconductor wafer which has a surface having a height difference of at least 30  $\mu\text{m}$ [,] and [which is worked] working the semiconductor wafer surface by grinding the back of the semiconductor wafer while protecting the semiconductor wafer surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate exhibiting a maximum value of dynamic viscoelasticity  $\tan \delta$  of 0.78 to 1.61 at a temperature ranging from  $-5$  to  $80^{\circ}\text{C}$ .

8. [The] A method [as claimed in claim 4, wherein the adherend is a] of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of a semiconductor wafer which has a surface having a height difference of at least 30  $\mu\text{m}$ [,] and [which is worked] working the semiconductor wafer surface by grinding the

back of the semiconductor wafer while protecting the semiconductor wafer surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate having a thickness and Young's modulus whose product is in the range of 0.5 to 100 kg/cm and said substrate exhibiting a maximum value of dynamic viscoelasticity  $\tan \delta$  of 0.78 to 1.61 at a temperature ranging from  $-5$  to  $80^{\circ}\text{C}$ .